

INTERNATIONAL STANDARD

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Single crystal wafers for surface acoustic wave (SAW) device applications – Specifications and measuring methods

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INTERNATIONAL ELECTROTECHNICAL COMMISSION

**SINGLE CRYSTAL WAFERS FOR SURFACE ACOUSTIC
WAVE (SAW) DEVICE APPLICATIONS –
SPECIFICATIONS AND MEASURING METHODS**

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Full information on the voting for the approval of this standard can be found in the report on voting indicated in the above table.

This publication has been drafted in accordance with the ISO/IEC Directives, Part 2.

The committee has decided that the contents of this publication will remain unchanged until the maintenance result date indicated on the IEC web site under "<http://webstore.iec.ch>" in the data related to the specific publication. At this date, the publication will be

- reconfirmed,
- withdrawn,
- replaced by a revised edition, or
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INTRODUCTION

A variety of piezoelectric materials are used for surface acoustic wave (SAW) filter and resonator applications. Prior to the 1996 Rotterdam IEC TC 49 meeting, wafer specifications were typically negotiated between users and suppliers. During the meeting a proposal was announced to address wafer standardization. This document has been prepared in order to provide industry standard technical specifications for manufacturing piezoelectric single crystal wafers to be used in surface acoustic wave devices.

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SINGLE CRYSTAL WAFERS FOR SURFACE ACOUSTIC WAVE (SAW) DEVICE APPLICATIONS – SPECIFICATIONS AND MEASURING METHODS

1 Scope

This International Standard applies to the manufacture of synthetic quartz, lithium niobate (LN), lithium tantalate (LT), lithium tetraborate (LBO), and lanthanum gallium silicate (LGS) single crystal wafers intended for use as substrates in the manufacture of surface acoustic wave (SAW) filters and resonators.

2 Normative references

The following referenced documents are indispensable for the application of this document. For dated references, only the edition cited applies. For undated references, the latest edition of the referenced document (including any amendments) applies.

IEC 60758, *Synthetic quartz crystal – Specifications and guide to the use*

IEC 60410, *Sampling plans and procedures inspection by attributes*

ISO 4287, *Geometrical Product Specifications (GPS) – Surface texture: Profile method – Terms, definitions and surface texture parameters*